

“Comparison of strained SiGe heterostructure-on-insulator (0 0 1) and (1 1 0) PMOSFETs : Characteristics, mobility, and ON current”. Pham A-T, Zhao Q-T, Jungemann C, Meinerzhagen B, Mantl S, Sorée B, Pourtois G, Solid state electronics **65-66**, 64 (2011). <http://doi.org/10.1016/j.sse.2011.06.021>